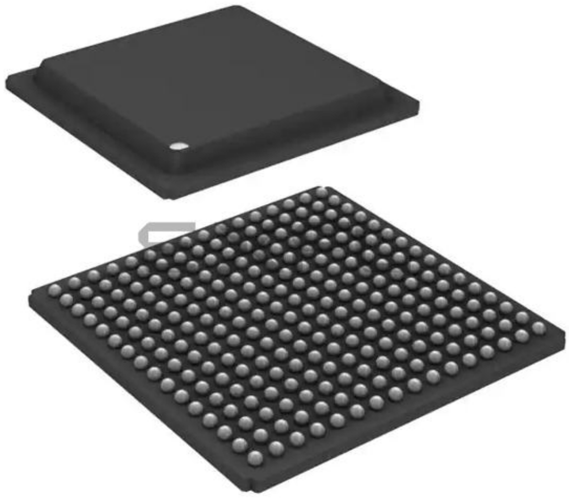
NXP USA Inc. - MPC850DECZQ50BU Datasheet



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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	MPC8xx
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	50MHz
Co-Processors/DSP	Communications; CPM
RAM Controllers	DRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	3.3V
Operating Temperature	-40°C ~ 95°C (TA)
Security Features	-
Package / Case	256-BBGA
Supplier Device Package	256-PBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc850deczq50bu

  - 2-Kbyte instruction cache and 1-Kbyte data cache (Harvard architecture)
    - Caches are two-way, set-associative
    - Physically addressed
    - Cache blocks can be updated with a 4-word line burst
    - Least-recently used (LRU) replacement algorithm
    - Lockable one-line granularity
  - Memory management units (MMUs) with 8-entry translation lookaside buffers (TLBs) and fully-associative instruction and data TLBs
  - MMUs support multiple page sizes of 4 Kbytes, 16 Kbytes, 256 Kbytes, 512 Kbytes, and 8 Mbytes; 16 virtual address spaces and eight protection groups
- Advanced on-chip emulation debug mode
- Data bus dynamic bus sizing for 8, 16, and 32-bit buses
  - Supports traditional 68000 big-endian, traditional x86 little-endian and modified little-endian memory systems
  - Twenty-six external address lines
- Completely static design (0–80 MHz operation)
- System integration unit (SIU)
  - Hardware bus monitor
  - Spurious interrupt monitor
  - Software watchdog
  - Periodic interrupt timer
  - Low-power stop mode
  - Clock synthesizer
  - Decrementer, time base, and real-time clock (RTC) from the PowerPC architecture
  - Reset controller
  - IEEE 1149.1 test access port (JTAG)
- Memory controller (eight banks)
  - Glueless interface to DRAM single in-line memory modules (SIMMs), synchronous DRAM (SDRAM), static random-access memory (SRAM), electrically programmable read-only memory (EPROM), flash EPROM, etc.
  - Memory controller programmable to support most size and speed memory interfaces
  - Boot chip-select available at reset (options for 8, 16, or 32-bit memory)
  - Variable block sizes, 32 Kbytes to 256 Mbytes
  - Selectable write protection
  - On-chip bus arbiter supports one external bus master
  - Special features for burst mode support
- General-purpose timers
  - Four 16-bit timers or two 32-bit timers

  - Separate power supply input to operate internal logic at 2.2 V when operating at or below 25 MHz
  - Can be dynamically shifted between high frequency (3.3 V internal) and low frequency (2.2 V internal) operation
- Debug interface
  - Eight comparators: four operate on instruction address, two operate on data address, and two operate on data
  - The MPC850 can compare using the =, ≠, <, and > conditions to generate watchpoints
  - Each watchpoint can generate a breakpoint internally
- 3.3-V operation with 5-V TTL compatibility on all general purpose I/O pins.

3 Electrical and Thermal Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC850. Table 2 provides the maximum ratings.

Table 2. Maximum Ratings

(GND = 0V)

Rating	Symbol	Value	Unit
Supply voltage	VDDH	-0.3 to 4.0	V
	VDDL	-0.3 to 4.0	V
	KAPWR	-0.3 to 4.0	V
	VDDSYN	-0.3 to 4.0	V
Input voltage [1]	V_{in}	GND-0.3 to VDDH + 2.5 V	V
Junction temperature [2]	T_j	0 to 95 (standard) -40 to 95 (extended)	°C
Storage temperature range	T_{stg}	-55 to +150	°C

[1] Functional operating conditions are provided with the DC electrical specifications in Table 5. Absolute maximum ratings are stress ratings only; functional operation at the maxima is not guaranteed. Stress beyond those listed may affect device reliability or cause permanent damage to the device.
CAUTION: All inputs that tolerate 5 V cannot be more than 2.5 V greater than the supply voltage. This restriction applies to power-up and normal operation (that is, if the MPC850 is unpowered, voltage greater than 2.5 V must not be applied to its inputs).

[2] The MPC850, a high-frequency device in a BGA package, does not provide a guaranteed maximum ambient temperature. Only maximum junction temperature is guaranteed. It is the responsibility of the user to consider power dissipation and thermal management. Junction temperature ratings are the same regardless of frequency rating of the device.

This device contains circuitry protecting against damage due to high-static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for example, either GND or V_{CC}). Table 3 provides the package thermal characteristics for the MPC850.

4 Thermal Characteristics

Table 3 shows the thermal characteristics for the MPC850.

Table 3. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal resistance for BGA [1]	θ_{JA}	40 [2]	°C/W
	θ_{JA}	31 [3]	°C/W
	θ_{JA}	24 [4]	°C/W
Thermal Resistance for BGA (junction-to-case)	θ_{JC}	8	°C/W

[1] For more information on the design of thermal vias on multilayer boards and BGA layout considerations in general, refer to AN-1231/D, Plastic Ball Grid Array Application Note available from your local Freescale sales office.

[2] Assumes natural convection and a single layer board (no thermal vias).

[3] Assumes natural convection, a multilayer board with thermal vias[4], 1 watt MPC850 dissipation, and a board temperature rise of 20°C above ambient.

[4] Assumes natural convection, a multilayer board with thermal vias[4], 1 watt MPC850 dissipation, and a board temperature rise of 13°C above ambient.

$T_J = T_A + (P_D \bullet \theta_{JA})$

$P_D = (V_{DD} \bullet I_{DD}) + P_{I/O}$

where:

$P_{I/O}$ is the power dissipation on pins

Table 4 provides power dissipation information.

Table 4. Power Dissipation (P_D)

Characteristic	Frequency (MHz)	Typical [1]	Maximum [2]	Unit
Power Dissipation All Revisions (1:1) Mode	33	TBD	515	mW
	40	TBD	590	mW
	50	TBD	725	mW

[1] Typical power dissipation is measured at 3.3V

[2] Maximum power dissipation is measured at 3.65 V

Table 5 provides the DC electrical characteristics for the MPC850.

Table 5. DC Electrical Specifications

Characteristic	Symbol	Min	Max	Unit
Operating voltage at 40 MHz or less	VDDH, VDDL, KAPWR, VDDSYN	3.0	3.6	V
Operating voltage at 40 MHz or higher	VDDH, VDDL, KAPWR, VDDSYN	3.135	3.465	V
Input high voltage (address bus, data bus, EXTAL, EXTCLK, and all bus control/status signals)	VIH	2.0	3.6	V
Input high voltage (all general purpose I/O and peripheral pins)	VIH	2.0	5.5	V

Table 5. DC Electrical Specifications (continued)

Characteristic	Symbol	Min	Max	Unit
Input low voltage	VIL	GND	0.8	V
EXTAL, EXTCLK input high voltage	VIHC	0.7*(VCC)	VCC+0.3	V
Input leakage current, Vin = 5.5 V (Except TMS, TRST, DSCK and DSDI pins)	I_{in}	—	100	µA
Input leakage current, Vin = 3.6V (Except TMS, TRST, DSCK and DSDI pins)	I_{In}	—	10	µA
Input leakage current, Vin = 0V (Except TMS, TRST, DSCK and DSDI pins)	I_{In}	—	10	µA
Input capacitance	C_{in}	—	20	pF
Output high voltage, IOH = -2.0 mA, VDDH = 3.0V except XTAL, XFC, and open-drain pins	VOH	2.4	—	V
Output low voltage CLKOUT [3] IOL = 3.2 mA [1] IOL = 5.3 mA [2] IOL = 7.0 mA PA[14]/USBOE, PA[12]/TXD2 IOL = 8.9 mA TS, TA, TEA, BI, BB, HRESET, SRESET	VOL	—	0.5	V

[1] A[6:31], TSIZ0/REG, TSIZ1, D[0:31], DP[0:3]/IRQ[3:6], RD/WR, BURST, RSV/IRQ2, IP_B[0:1]/IWP[0:1]/VFLS[0:1], IP_B2/IOIS16_B/AT2, IP_B3/IWP2/VF2, IP_B4/LWP0/VF0, IP_B5/LWP1/VF1, IP_B6/DSDI/AT0, IP_B7/PTR/AT3, PA[15]/USBRXD, PA[13]/RXD2, PA[9]/L1TXDA/SMRXD2, PA[8]/L1RXDA/SMTXD2, PA[7]/CLK1/TIN1/L1RCLKA/BRGO1, PA[6]/CLK2/TOUT1/TIN3, PA[5]/CLK3/TIN2/L1TCLKA/BRGO2, PA[4]/CLK4/TOUT2/TIN4, PB[31]/SPISEL, PB[30]/SPICLK/TXD3, PB[29]/SPIMOSI /RXD3, PB[28]/SPIMISO/BRGO3, PB[27]/I2CSDA/BRGO1, PB[26]/I2CSCL/BRGO2, PB[25]/SMTXD1/TXD3, PB[24]/SMRXD1/RXD3, PB[23]/SMSYN1/SDACK1, PB[22]/SMSYN2/SDACK2, PB[19]/L1ST1, PB[18]/RTS2/L1ST2, PB[17]/L1ST3, PB[16]/L1RQa/L1ST4, PC[15]/DREQ0/L1ST5, PC[14]/DREQ1/RTS2/L1ST6, PC[13]/L1ST7/RTS3, PC[12]/L1RQa/L1ST8, PC[11]/USBRXP, PC[10]/TGATE1/USBRXN, PC[9]/CTS2, PC[8]/CD2/TGATE1, PC[7]/USBTXP, PC[6]/USBTXN, PC[5]/CTS3/L1TSYNCA/SDACK1, PC[4]/CD3/L1RSYNCA, PD[15], PD[14], PD[13], PD[12], PD[11], PD[10], PD[9], PD[8], PD[7], PD[6], PD[5], PD[4], PD[3]

[2] BDIP/GPL_B5, BR, BG, FRZ/IRQ6, CS[0:5], CS6/CE1_B, CS7/CE2_B, WE0/BS_AB0/IORD, WE1/BS_AB1/IOWR, WE2/BS_AB2/PCOE, WE3/BS_AB3/PCWE, GPL_A0/GPL_B0, OE/GPL_A1/GPL_B1, GPL_A[2:3]/GPL_B[2:3]/CS[2:3], UPWAITA/GPL_A4/AS, UPWAITB/GPL_B4, GPL_A5, ALE_B/DSCK/AT1, OP2/MODCK1/STS, OP3/MODCK2/DSDO

3 The MPC850 IBIS model must be used to accurately model the behavior of the Clkout output driver for the full and half drive setting. Due to the nature of the Clkout output buffer, IOH and IOL for Clkout should be extracted from the IBIS model at any output voltage level.

5 Power Considerations

The average chip-junction temperature, T_J, in °C can be obtained from the equation:

$T_J = T_A + (P_D \bullet \theta_{JA})$(1)

where

T_A = Ambient temperature, °C

θ_{JA} = Package thermal resistance, junction to ambient, °C/W

$P_D = P_{INT} + P_{I/O}$

$P_{INT} = I_{DD} \times V_{DD}$, watts—chip internal power

$P_{I/O}$ = Power dissipation on input and output pins—user determined

For most applications $P_{I/O} < 0.3 \bullet P_{INT}$ and can be neglected. If $P_{I/O}$ is neglected, an approximate relationship between P_D and T_J is:

$P_D = K \div (T_J + 273°C)$(2)

Solving equations (1) and (2) for K gives:

$K = P_D \bullet (T_A + 273°C) + \theta_{JA} \bullet P_D^2$(3)

where K is a constant pertaining to the particular part. K can be determined from equation (3) by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving equations (1) and (2) iteratively for any value of T_A.

5.1 Layout Practices

Each V_{CC} pin on the MPC850 should be provided with a low-impedance path to the board's supply. Each GND pin should likewise be provided with a low-impedance path to ground. The power supply pins drive distinct groups of logic on chip. The V_{CC} power supply should be bypassed to ground using at least four 0.1 µF by-pass capacitors located as close as possible to the four sides of the package. The capacitor leads and associated printed circuit traces connecting to chip V_{CC} and GND should be kept to less than half an inch per capacitor lead. A four-layer board is recommended, employing two inner layers as V_{CC} and GND planes.

All output pins on the MPC850 have fast rise and fall times. Printed circuit (PC) trace interconnection length should be minimized in order to minimize undershoot and reflections caused by these fast output switching times. This recommendation particularly applies to the address and data busses. Maximum PC trace lengths of six inches are recommended. Capacitance calculations should consider all device loads as well as parasitic capacitances due to the PC traces. Attention to proper PCB layout and bypassing becomes especially critical in systems with higher capacitive loads because these loads create higher transient currents in the V_{CC} and GND circuits. Pull up all unused inputs or signals that will be inputs during reset. Special care should be taken to minimize the noise levels on the PLL supply pins.

6 Bus Signal Timing

Table 6 provides the bus operation timing for the MPC850 at 50 MHz, 66 MHz, and 80 MHz. Timing information for other bus speeds can be interpolated by equation using the MPC850 Electrical Specifications Spreadsheet found at http://www.mot.com/netcomm.

The maximum bus speed supported by the MPC850 is 50 MHz. Higher-speed parts must be operated in half-speed bus mode (for example, an MPC850 used at 66 MHz must be configured for a 33 MHz bus).

The timing for the MPC850 bus shown assumes a 50-pF load. This timing can be derated by 1 ns per 10 pF. Derating calculations can also be performed using the MPC850 Electrical Specifications Spreadsheet.

Table 6. Bus Operation Timing [1] (continued)

Num	Characteristic	50 MHz		66 MHz		80 MHz		FFACT	Cap Load (default 50 pF)	Unit
		Min	Max	Min	Max	Min	Max			
B28c	CLKOUT falling edge to $\overline{\text{WE[0–3]}}$ negated GPCM write access TRLX = 0,1 CSNT = 1 write access TRLX = 0, CSNT = 1, EBDF = 1	7.00	14.00	11.00	18.00	9.00	16.00	0.375	50.00	ns
B28d	CLKOUT falling edge to $\overline{\text{CS}}$ negated GPCM write access TRLX = 0,1 CSNT = 1, ACS = 10 or ACS = 11, EBDF = 1	—	14.00	—	18.00	—	16.00	0.375	50.00	ns
B29	$\overline{\text{WE[0–3]}}$ negated to D[0–31], DP[0–3] high-Z GPCM write access, CSNT = 0	3.00	—	6.00	—	4.00	—	0.250	50.00	ns
B29a	$\overline{\text{WE[0–3]}}$ negated to D[0–31], DP[0–3] high-Z GPCM write access, TRLX = 0 CSNT = 1, EBDF = 0	8.00	—	13.00	—	11.00	—	0.500	50.00	ns
B29b	$\overline{\text{CS}}$ negated to D[0–31], DP[0–3], high-Z GPCM write access, ACS = 00, TRLX = 0 & CSNT = 0	3.00	—	6.00	—	4.00	—	0.250	50.00	ns
B29c	$\overline{\text{CS}}$ negated to D[0–31], DP[0–3] high-Z GPCM write access, TRLX = 0, CSNT = 1, ACS = 10 or ACS = 11, EBDF = 0	8.00	—	13.00	—	11.00	—	0.500	50.00	ns
B29d	$\overline{\text{WE[0–3]}}$ negated to D[0–31], DP[0–3] high-Z GPCM write access, TRLX = 1, CSNT = 1, EBDF = 0	28.00	—	43.00	—	36.00	—	1.500	50.00	ns
B29e	$\overline{\text{CS}}$ negated to D[0–31], DP[0–3] high-Z GPCM write access, TRLX = 1, CSNT = 1, ACS = 10 or ACS = 11, EBDF = 0	28.00	—	43.00	—	36.00	—	1.500	50.00	ns
B29f	$\overline{\text{WE[0–3]}}$ negated to D[0–31], DP[0–3] high-Z GPCM write access TRLX = 0, CSNT = 1, EBDF = 1	5.00	—	9.00	—	7.00	—	0.375	50.00	ns
B29g	$\overline{\text{CS}}$ negated to D[0–31], DP[0–3] high-Z GPCM write access TRLX = 0, CSNT = 1, ACS = 10 or ACS = 11, EBDF = 1	5.00	—	9.00	—	7.00	—	0.375	50.00	ns

Table 6. Bus Operation Timing [1] (continued)

Num	Characteristic	50 MHz		66 MHz		80 MHz		FFACT	Cap Load (default 50 pF)	Unit
		Min	Max	Min	Max	Min	Max			
B42	CLKOUT rising edge to $\overline{\text{TS}}$ valid (hold time)	2.00	—	2.00	—	2.00	—	—	50.00	ns
B43	$\overline{\text{AS}}$ negation to memory controller signals negation	—	TBD	—	TBD	TBD	—	—	50.00	ns

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[1] The minima provided assume a 0 pF load, whereas maxima assume a 50pF load. For frequencies not marked on the part, new bus timing must be calculated for all frequency-dependent AC parameters. Frequency-dependent AC parameters are those with an entry in the FFactor column. AC parameters without an FFactor entry do not need to be calculated and can be taken directly from the frequency column corresponding to the frequency marked on the part. The following equations should be used in these calculations.

For a frequency F, the following equations should be applied to each one of the above parameters:

For minima:

$$D = \frac{\text{FFACTOR x 1000}}{F} + (D_{50} - \text{20 x FFACTOR})$$

For maxima:

$$D = \frac{\text{FFACTOR x 1000}}{F} + (D_{50} - \text{20 x FFACTOR}) + \text{1ns(CAP LOAD - 50) / 10}$$

where:

D is the parameter value to the frequency required in ns

F is the operation frequency in MHz

D_{50} is the parameter value defined for 50 MHz

CAP LOAD is the capacitance load on the signal in question.

FFACTOR is the one defined for each of the parameters in the table.

[2] Phase and frequency jitter performance results are valid only if the input jitter is less than the prescribed value.

[3] If the rate of change of the frequency of EXTAL is slow (i.e. it does not jump between the minimum and maximum values in one cycle) or the frequency of the jitter is fast (i.e., it does not stay at an extreme value for a long time) then the maximum allowed jitter on EXTAL can be up to 2%.

[4] The timing for $\overline{\text{BR}}$ output is relevant when the MPC850 is selected to work with external bus arbiter. The timing for $\overline{\text{BG}}$ output is relevant when the MPC850 is selected to work with internal bus arbiter.

[5] The setup times required for $\overline{\text{TA}}$, $\overline{\text{TEA}}$, and $\overline{\text{BI}}$ are relevant only when they are supplied by an external device (and not when the memory controller or the PCMCIA interface drives them).

[6] The timing required for $\overline{\text{BR}}$ input is relevant when the MPC850 is selected to work with the internal bus arbiter. The timing for $\overline{\text{BG}}$ input is relevant when the MPC850 is selected to work with the external bus arbiter.

[7] The D[0–31] and DP[0–3] input timings B20 and B21 refer to the rising edge of the CLKOUT in which the $\overline{\text{TA}}$ input signal is asserted.

[8] The D[0:31] and DP[0:3] input timings B20 and B21 refer to the falling edge of CLKOUT. This timing is valid only for read accesses controlled by chip-selects controlled by the UPM in the memory controller, for data beats where DLT3 = 1 in the UPM RAM words. (This is only the case where data is latched on the falling edge of CLKOUT.

[9] The timing B30 refers to $\overline{\text{CS}}$ when ACS = '00' and to $\overline{\text{WE[0:3]}}$ when CSNT = '0'.

[10] The signal UPWAIT is considered asynchronous to CLKOUT and synchronized internally. The timings specified in B37 and B38 are specified to enable the freeze of the UPM output signals.

[11] The $\overline{\text{AS}}$ signal is considered asynchronous to CLKOUT.

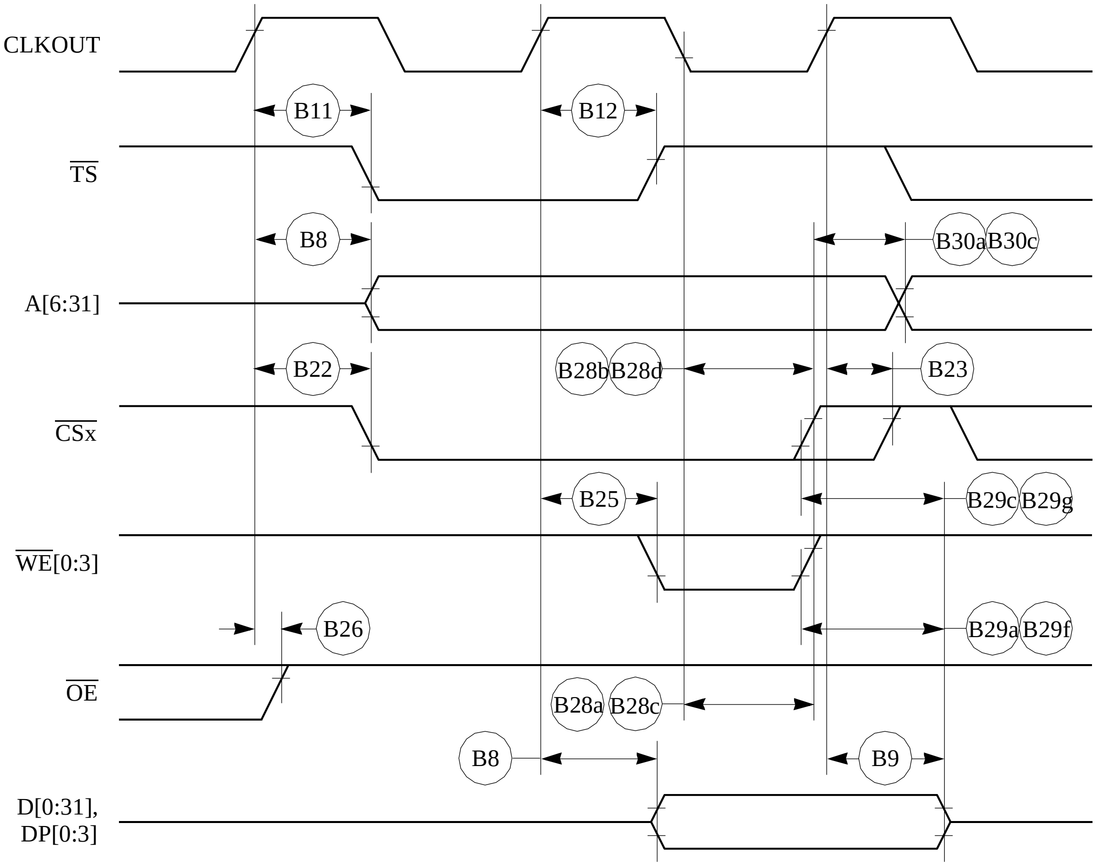


Figure 14. External Bus Write Timing (GPCM Controlled—TRLX = 0, CSNT = 1)

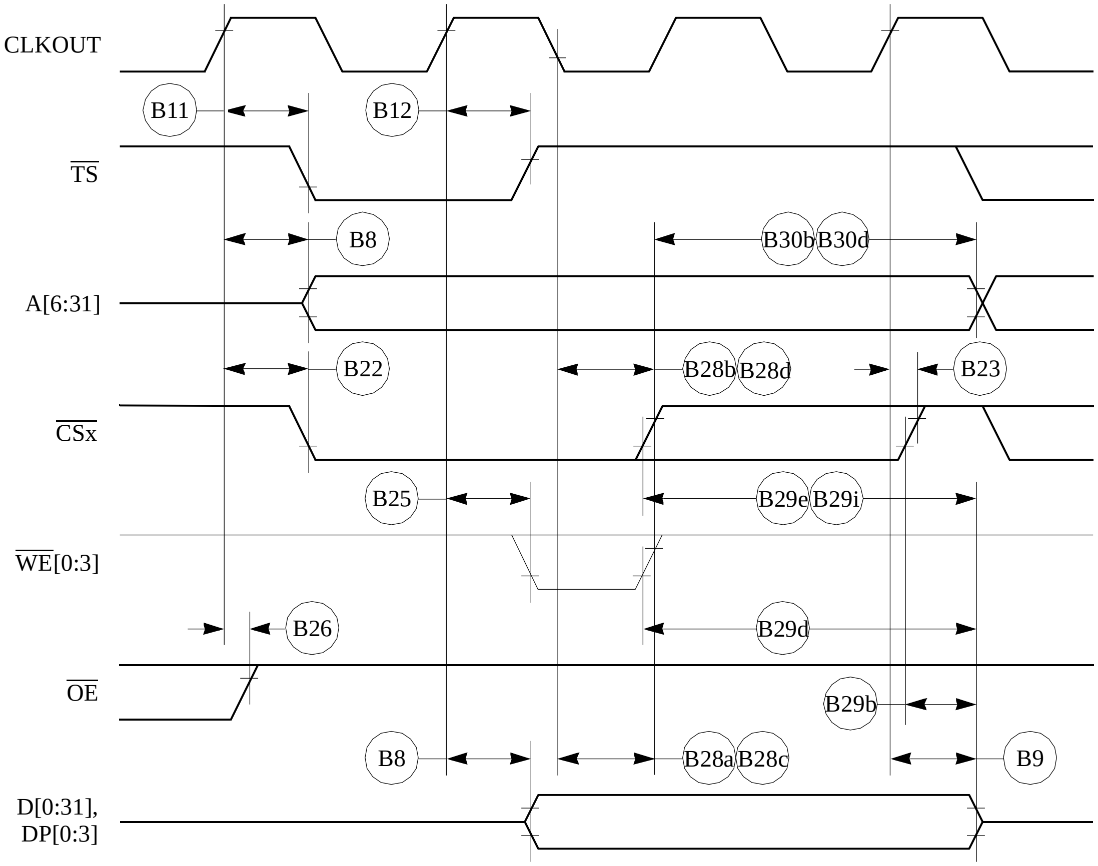


Figure 15. External Bus Write Timing (GPCM Controlled—TRLX = 1, CSNT = 1)

Figure 17 provides the timing for the asynchronous asserted UPWAIT signal controlled by the UPM.

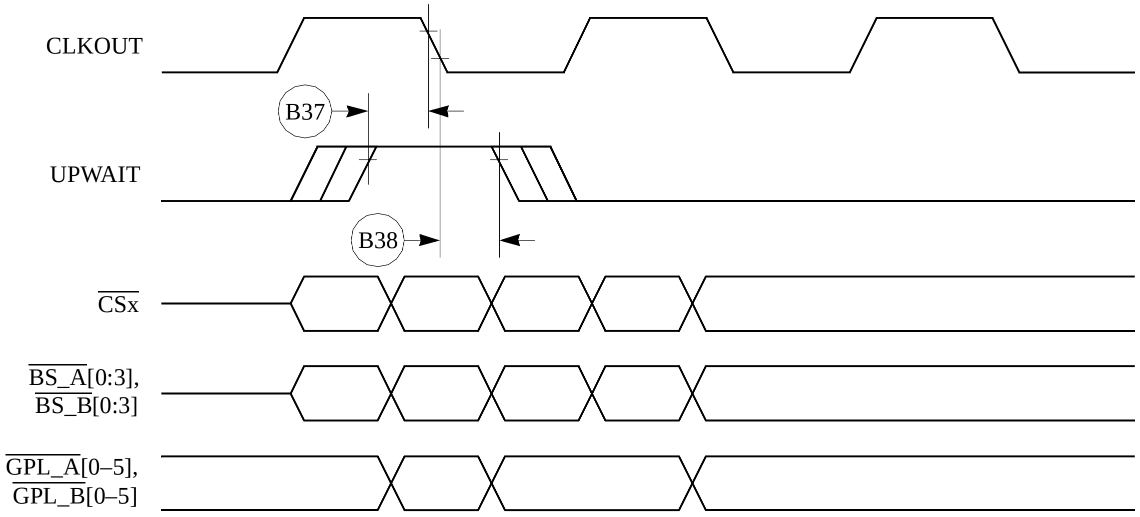


Figure 17. Asynchronous UPWAIT Asserted Detection in UPM Handled Cycles Timing

Figure 18 provides the timing for the asynchronous negated UPWAIT signal controlled by the UPM.

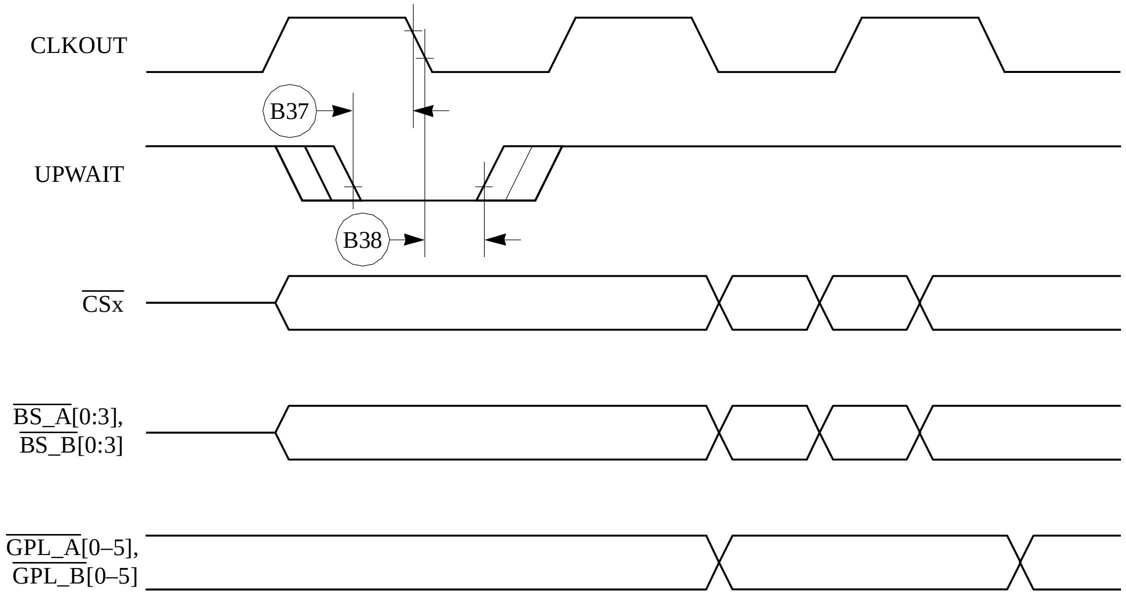


Figure 18. Asynchronous $\overline{\text{UPWAIT}}$ Negated Detection in UPM Handled Cycles Timing

Figure 24 provides the PCMCIA access cycle timing for the external bus read.

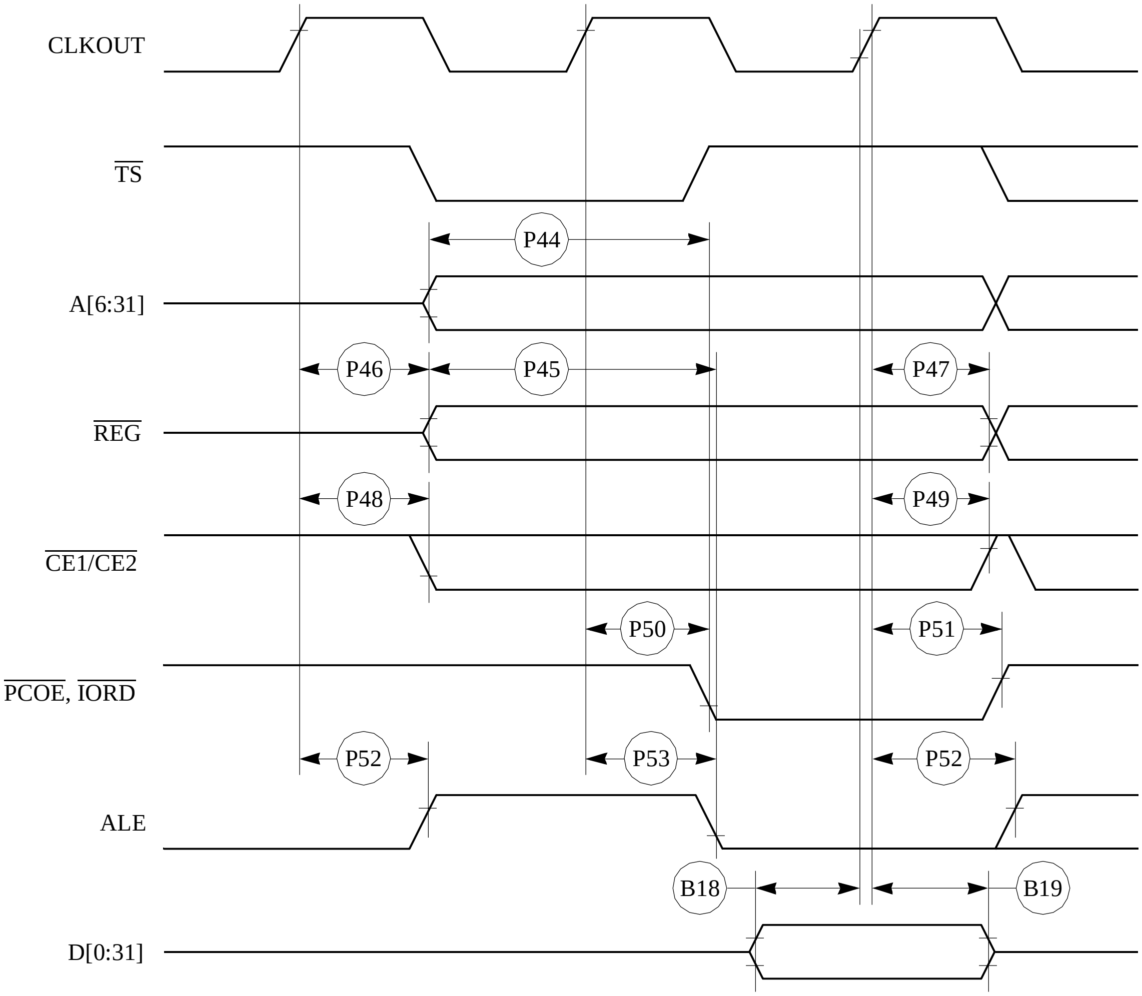


Figure 24. PCMCIA Access Cycles Timing External Bus Read

Figure 33 provides the reset timing for the debug port configuration.

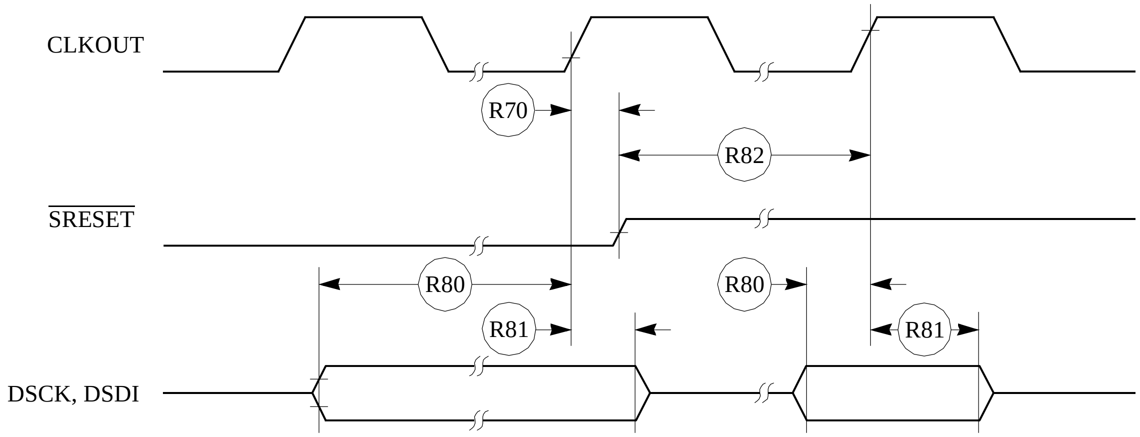


Figure 33. Reset Timing—Debug Port Configuration

7 IEEE 1149.1 Electrical Specifications

Table 12 provides the JTAG timings for the MPC850 as shown in Figure 34 to Figure 37.

Table 12. JTAG Timing

Num	Characteristic	50 MHz		66MHz		80 MHz		Unit
		Min	Max	Min	Max	Min	Max	
J82	TCK cycle time	100.00	—	100.00	—	100.00	—	ns
J83	TCK clock pulse width measured at 1.5 V	40.00	—	40.00	—	40.00	—	ns
J84	TCK rise and fall times	0.00	10.00	0.00	10.00	0.00	10.00	ns
J85	TMS, TDI data setup time	5.00	—	5.00	—	5.00	—	ns
J86	TMS, TDI data hold time	25.00	—	25.00	—	25.00	—	ns
J87	TCK low to TDO data valid	—	27.00	—	27.00	—	27.00	ns
J88	TCK low to TDO data invalid	0.00	—	0.00	—	0.00	—	ns
J89	TCK low to TDO high impedance	—	20.00	—	20.00	—	20.00	ns
J90	$\overline{\text{TRST}}$ assert time	100.00	—	100.00	—	100.00	—	ns
J91	$\overline{\text{TRST}}$ setup time to TCK low	40.00	—	40.00	—	40.00	—	ns
J92	TCK falling edge to output valid	—	50.00	—	50.00	—	50.00	ns
J93	TCK falling edge to output valid out of high impedance	—	50.00	—	50.00	—	50.00	ns
J94	TCK falling edge to output high impedance	—	50.00	—	50.00	—	50.00	ns
J95	Boundary scan input valid to TCK rising edge	50.00	—	50.00	—	50.00	—	ns
J96	TCK rising edge to boundary scan input invalid	50.00	—	50.00	—	50.00	—	ns

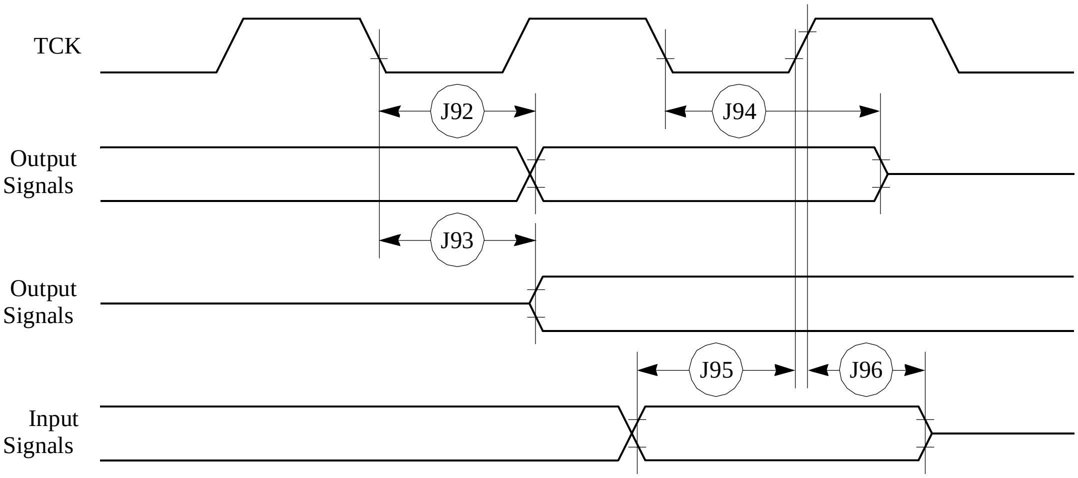


Figure 37. Boundary Scan (JTAG) Timing Diagram

8 CPM Electrical Characteristics

This section provides the AC and DC electrical specifications for the communications processor module (CPM) of the MPC850.

8.1 PIO AC Electrical Specifications

Table 13 provides the parallel I/O timings for the MPC850 as shown in Figure 38.

Table 13. Parallel I/O Timing

Num	Characteristic	All Frequencies		Unit
		Min	Max	
29	Data-in setup time to clock high	15	—	ns
30	Data-in hold time from clock high	7.5	—	ns
31	Clock low to data-out valid (CPU writes data, control, or direction)	—	25	ns

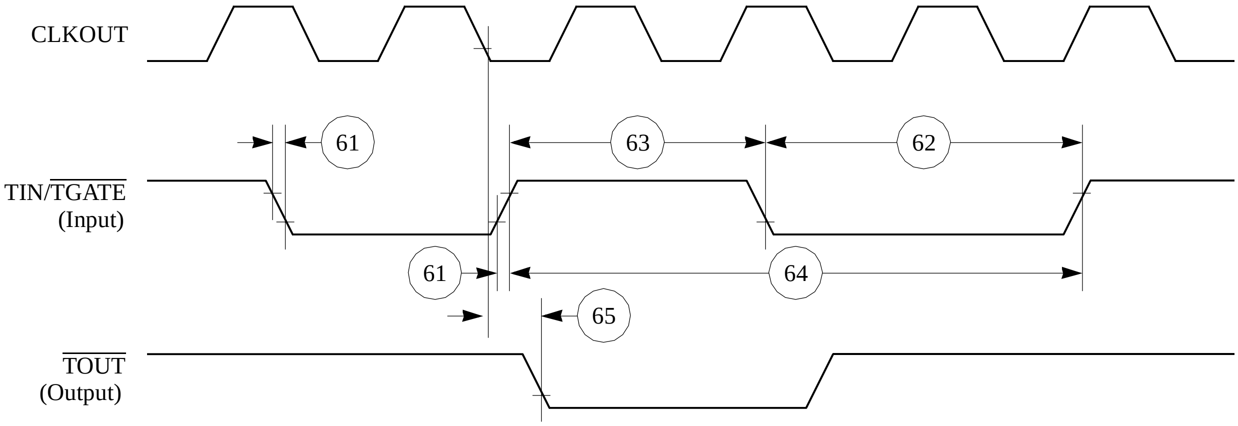


Figure 44. CPM General-Purpose Timers Timing Diagram

8.5 Serial Interface AC Electrical Specifications

Table 17 provides the serial interface timings as shown in Figure 45 to Figure 49.

Table 17. SI Timing

Num	Characteristic	All Frequencies		Unit
		Min	Max	
70	L1RCLK, L1TCLK frequency (DSC = 0) [1, 2]	—	SYNCCLK/2.5	MHz
71	L1RCLK, L1TCLK width low (DSC = 0) [2]	P + 10	—	ns
71a	L1RCLK, L1TCLK width high (DSC = 0) [3]	P + 10	—	ns
72	L1TXD, L1ST*n*, $\overline{\text{L1RQ}}$, L1xCLKO rise/fall time	—	15.00	ns
73	L1RSYNC, L1TSYNC valid to L1xCLK edge Edge (SYNC setup time)	20.00	—	ns
74	L1xCLK edge to L1RSYNC, L1TSYNC, invalid (SYNC hold time)	35.00	—	ns
75	L1RSYNC, L1TSYNC rise/fall time	—	15.00	ns
76	L1RXD valid to L1xCLK edge (L1RXD setup time)	17.00	—	ns
77	L1xCLK edge to L1RXD invalid (L1RXD hold time)	13.00	—	ns
78	L1xCLK edge to L1ST*n* valid [4]	10.00	45.00	ns
78A	L1SYNC valid to L1ST*n* valid	10.00	45.00	ns
79	L1xCLK edge to L1ST*n* invalid	10.00	45.00	ns
80	L1xCLK edge to L1TXD valid	10.00	55.00	ns
80A	L1TSYNC valid to L1TXD valid [4]	10.00	55.00	ns
81	L1xCLK edge to L1TXD high impedance	0.00	42.00	ns

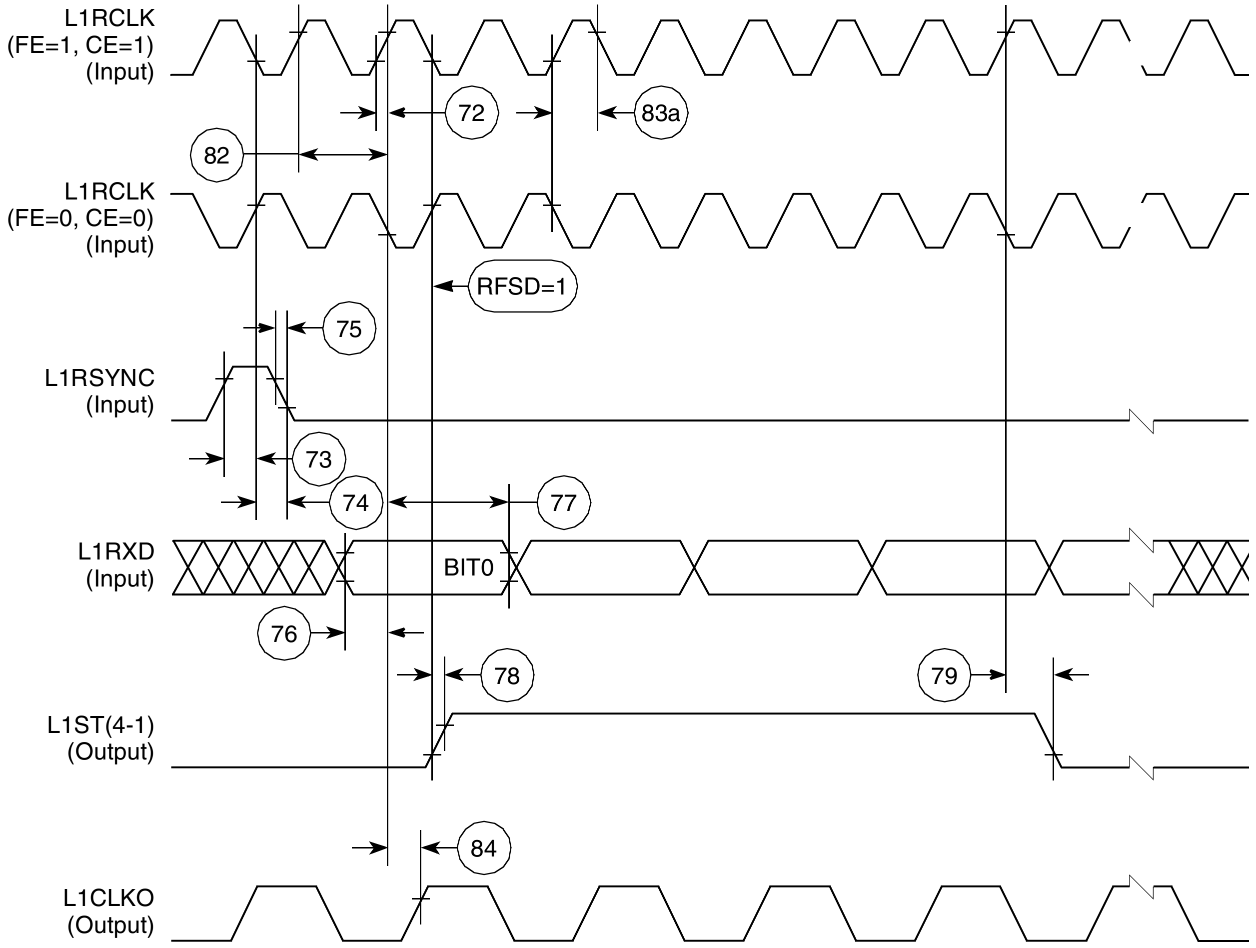
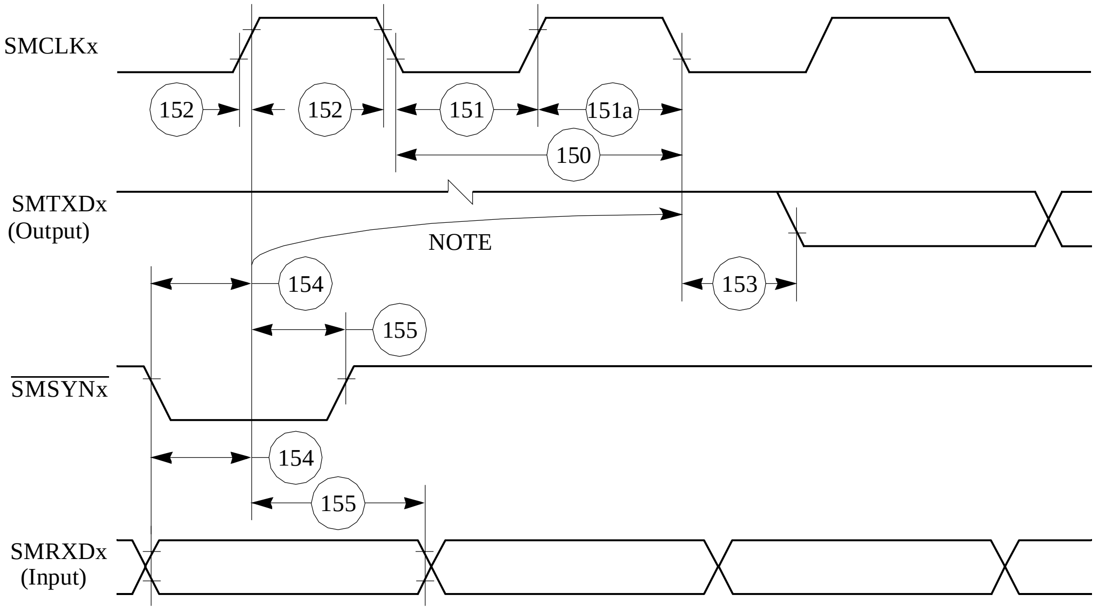


Figure 46. SI Receive Timing with Double-Speed Clocking (DSC = 1)



NOTE:
1. This delay is equal to an integer number of character-length clocks.

Figure 56. SMC Transparent Timing Diagram

8.9 SPI Master AC Electrical Specifications

Table 22 provides the SPI master timings as shown in Figure 57 and Figure 58.

Table 22. SPI Master Timing

Num	Characteristic	All Frequencies		Unit
		Min	Max	
160	MASTER cycle time	4	1024	t_{cyc}
161	MASTER clock (SCK) high or low time	2	512	t_{cyc}
162	MASTER data setup time (inputs)	50.00	—	ns
163	Master data hold time (inputs)	0.00	—	ns
164	Master data valid (after SCK edge)	—	20.00	ns
165	Master data hold time (outputs)	0.00	—	ns
166	Rise time output	—	15.00	ns
167	Fall time output	—	15.00	ns

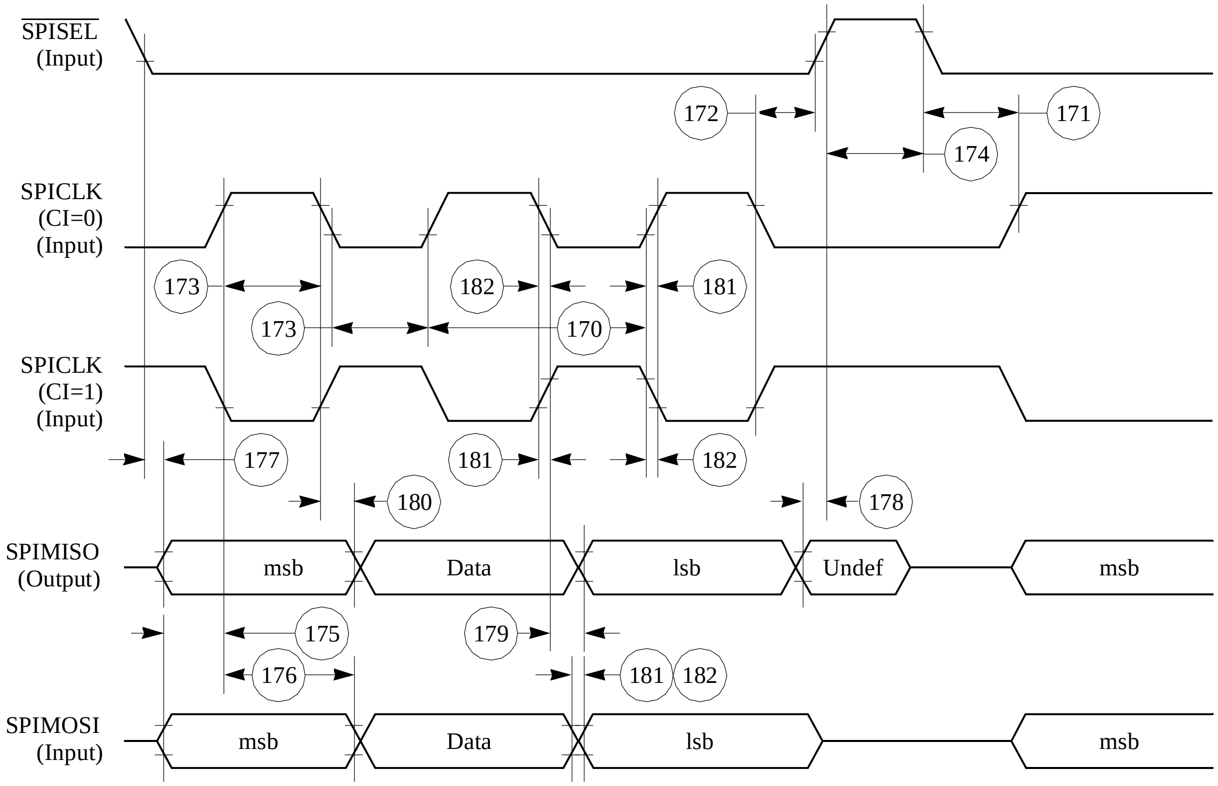


Figure 59. SPI Slave (CP = 0) Timing Diagram

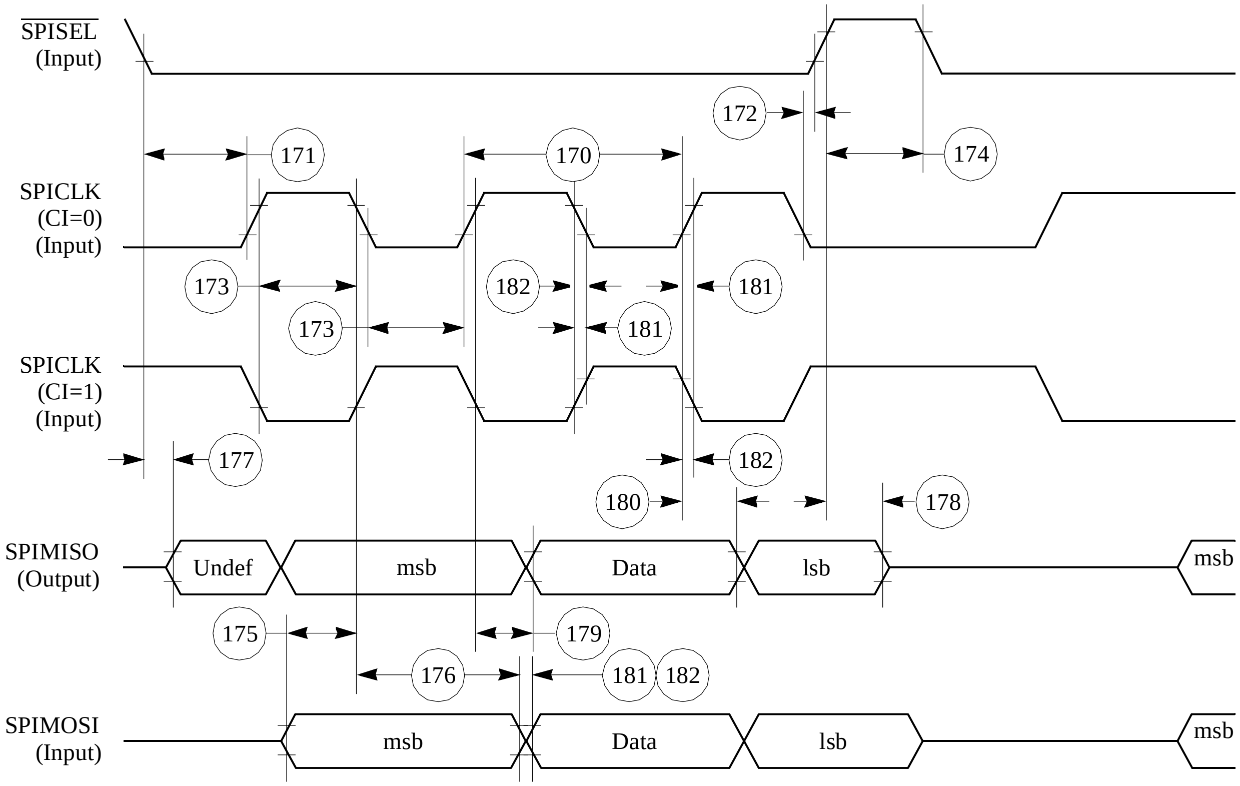


Figure 60. SPI Slave (CP = 1) Timing Diagram

8.11 I²C AC Electrical Specifications

Table 24 provides the I^{2}C (SCL < 100 KHz) timings.

Table 24. I²C Timing (SCL < 100 KHz)

Num	Characteristic	All Frequencies		Unit
		Min	Max	
200	SCL clock frequency (slave)	0.00	100.00	KHz
200	SCL clock frequency (master) [1]	1.50	100.00	KHz
202	Bus free time between transmissions	4.70	—	µs
203	Low period of SCL	4.70	—	µs
204	High period of SCL	4.00	—	µs
205	Start condition setup time	4.70	—	µs
206	Start condition hold time	4.00	—	µs
207	Data hold time	0.00	—	µs
208	Data setup time	250.00	—	ns
209	SDL/SCL rise time	—	1.00	µs

Table 24. I^{2}C Timing (SCL < 100 KHz) (CONTINUED)

Num	Characteristic	All Frequencies		Unit
		Min	Max	
210	SDL/SCL fall time	—	300.00	ns
211	Stop condition setup time	4.70	—	µs

[1] SCL frequency is given by SCL = BRGCLK_frequency / ((BRG register + 3) * pre_scaler * 2). The ratio SyncClk/(BRGCLK/pre_scaler) must be greater or equal to 4/1.

Table 25 provides the I^{2}C (SCL > 100 KHz) timings.

Table 25. I^{2}C Timing (SCL > 100 KHz)

Num	Characteristic	Expression	All Frequencies		Unit
			Min	Max	
200	SCL clock frequency (slave)	fSCL	0	BRGCLK/48	Hz
200	SCL clock frequency (master) [1]	fSCL	BRGCLK/16512	BRGCLK/48	Hz
202	Bus free time between transmissions		1/(2.2 * fSCL)	—	s
203	Low period of SCL		1/(2.2 * fSCL)	—	s
204	High period of SCL		1/(2.2 * fSCL)	—	s
205	Start condition setup time		1/(2.2 * fSCL)	—	s
206	Start condition hold time		1/(2.2 * fSCL)	—	s
207	Data hold time		0	—	s
208	Data setup time		1/(40 * fSCL)	—	s
209	SDL/SCL rise time		—	1/(10 * fSCL)	s
210	SDL/SCL fall time		—	1/(33 * fSCL)	s
211	Stop condition setup time		1/2(2.2 * fSCL)	—	s

[1] SCL frequency is given by SCL = BrgClk_frequency / ((BRG register + 3) * pre_scaler * 2). The ratio SyncClk/(Brg_Clk/pre_scaler) must be greater or equal to 4/1.

Figure 61 shows the I^{2}C bus timing.

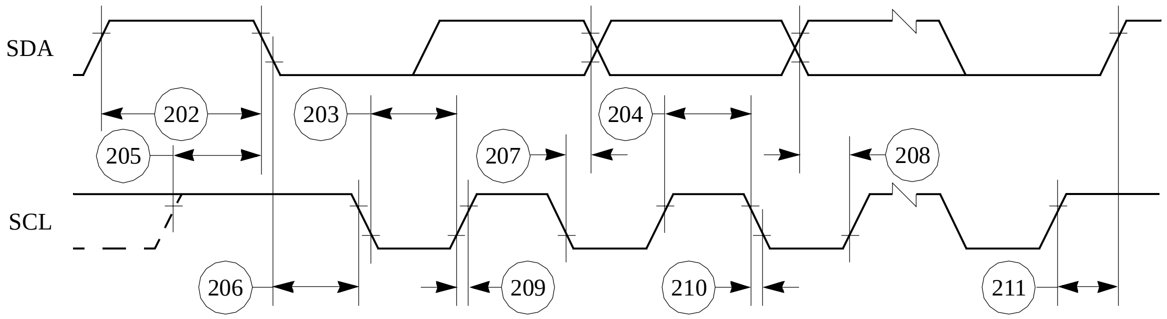


Figure 61. I^{2}C Bus Timing Diagram

Figure 63 shows the JEDEC pinout of the PBGA package as viewed from the top surface.

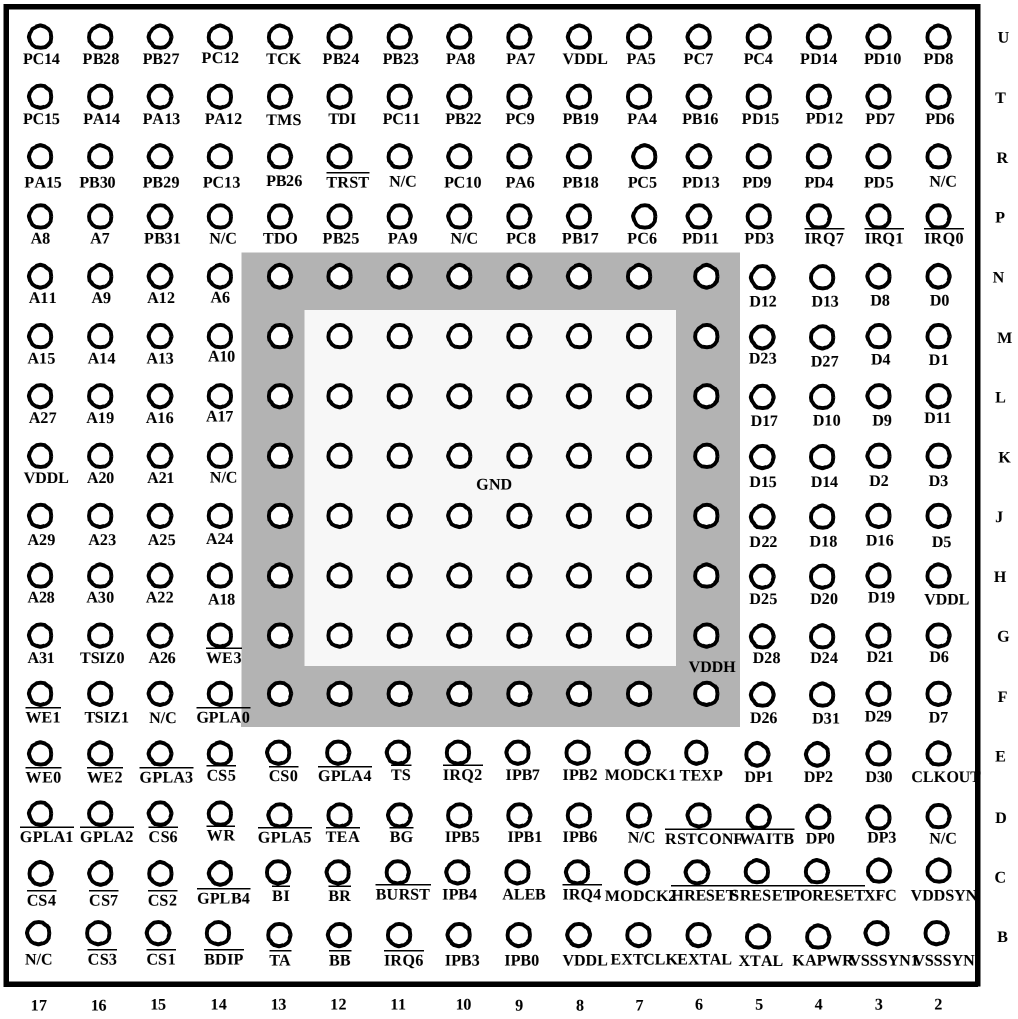


Figure 63. Pin Assignments for the PBGA (Top View)—JEDEC Standard

For more information on the printed circuit board layout of the PBGA package, including thermal via design and suggested pad layout, please refer to AN-1231/D, Plastic Ball Grid Array Application Note available from your local Freescale sales office.